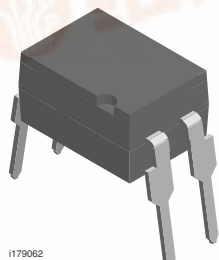
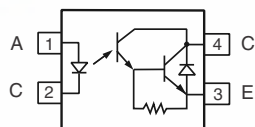


Optocoupler, AC Input, 5300 V_{RMS}



H79062



DESCRIPTION

The SFH620AA/SFH620AGB features a high current transfer ratio, low coupling capacitance and high isolation voltage. These couplers have a GaAs infrared emitting diode emitter, which is optically coupled to a silicon planar phototransistor detector, and is incorporated in a plastic DIP-4 package.

The coupling devices are designed for signal transmission between two electrically separated circuits.

The couplers are end-stackable with 2.54 mm lead spacing. Creepage and clearance distances of > 8.0 mm are achieved with option 6. This version complies with IEC 60950 (DIN VDE 0805) for reinforced insulation up to an operation voltage of 400 V_{RMS} or DC.

FEATURES

- High current transfer ratios
 - at 5 mA: 50 to 600 %
 - at 1.0 mA: 45 % typical (> 13)
- Low CTR degradation
- Good CTR linearity depending on forward current
- Isolation test voltage, 5300 V_{RMS}
- High collector emitter voltage, V_{CEO} = 70 V
- Low saturation voltage
- Fast switching times
- Temperature stable
- Low coupling capacitance
- End stackable, 0.100" (2.54 mm) spacing
- High common mode interference immunity (unconnected base)
- SMD option, see SFH620A/SFH6206 data sheet
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC


RoHS
COMPLIANT

AGENCY APPROVALS

- UL1577, file no. E52744 system code H or J, double protection
- DIN EN 60747-5-5 (VDE 0884) available with option 1
- CSA 93751
- BSI IEC 60950; IEC 60065

ORDER INFORMATION

PART	REMARKS
SFH620AA	CTR 50 % to 600 %, DIP-4
SFH620AGB	CTR 100 % to 600 %, DIP-4
SFH620AA-X009	CTR 50 % to 600 %, SMD-4 (option 9)
SFH620AGB-X007	CTR 100 % to 600 %, SMD-4 (option 7)
SFH620AGB-X009	CTR 100 % to 600 %, SMD-4 (option 9)

Note

For additional information on the available options refer to option information.

ABSOLUTE MAXIMUM RATINGS ⁽¹⁾				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
INPUT				
Reverse voltage		V _R	6.0	V
DC forward current		I _F	± 60	mA
Surge forward current	t _p ≤ 1.0 μs	I _{FSM}	± 2.5	A
Total power dissipation		P _{diss}	100	mW
OUTPUT				
Collector emitter voltage		V _{CE}	70	V
Emitter collector voltage		V _{EC}	7	V
Collector current		I _C	50	mA
	t _p ≤ 1.0 ms	I _C	100	mA
Power dissipation		P _{diss}	150	mW
COUPLER				
Isolation test voltage between emitter and detector		V _{ISO}	5300	V _{RMS}
Creepage distance			≥ 7	mm
Clearance distance			≥ 7	mm
Insulation thickness between emitter and detector			0.4	mm
Comparative tracking index per DIN IEC 112/VDE 0303 part 1		CTI	175	
Isolation resistance	V _{IO} = 500 V, T _{amb} = 25 °C	R _{IO}	≥ 10 ¹²	Ω
	V _{IO} = 500 V, T _{amb} = 100 °C	R _{IO}	≥ 10 ¹¹	Ω
Storage temperature		T _{stg}	- 55 to + 150	°C
Ambient temperature		T _{amb}	- 55 to +100	°C
Junction temperature		T _J	100	°C
Soldering temperature ⁽²⁾	max. 10 s, dip soldering distance to seating plane ≥ 1.5 mm	T _{slid}	260	°C

Notes

⁽¹⁾ T_{amb} = 25 °C, unless otherwise specified.

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

⁽²⁾ Refer to reflow profile for soldering conditions for surface mounted devices (SMD). Refer to wave profile for soldering conditions for through hole devices (DIP).

ELECTRICAL CHARACTERISTICS							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
INPUT							
Forward voltage	I _F = ± 60 mA		V _F		1.25	1.65	V
Capacitance	V _R = 0 V, f = 1 MHz		C _O		50		pF
Thermal resistance			R _{thja}		750		K/W
OUTPUT							
Collector emitter capacitance	V _{CE} = 5 V, f = 1 MHz		C _{CE}		6.8		pF
Thermal resistance			R _{thja}		500		K/W
COUPLER							
Collector emitter saturation voltage	I _F = 10 mA, I _C = 2.5 mA		V _{CEsat}		0.25	0.4	V
Coupling capacitance			C _C		0.2		pF
Collector emitter leakage current	V _{CE} = 10 V	SFH620AA	I _{CEO}		10	100	nA
		SFH620AGB	I _{CEO}		10	100	nA

Note

T_{amb} = 25 °C, unless otherwise specified.

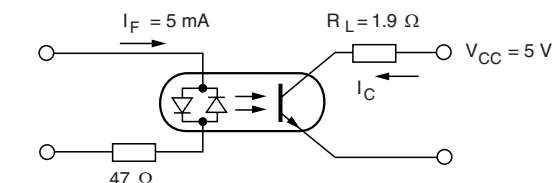
Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.

SFH620AA, SFH620AGB



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CURRENT TRANSFER RATIO							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
I_C/I_F	$I_F = \pm 5 \text{ mA}$, $V_{CE} = 5 \text{ V}$	SFH620AA			50 to 600		%
		SFH620AGB			100 to 600		%



isfh620aa_0

Fig. 1 - Switching Times (Typical Values)
Linear Operation (Saturated)

SWITCHING CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Turn-on time	$I_F = 5 \text{ mA}$, $R_L = 1.9 \text{ k}\Omega$, $V_{CC} = 5 \text{ V}$	t_{on}		2		μs
Turn-off time	$I_F = 5 \text{ mA}$, $R_L = 1.9 \text{ k}\Omega$, $V_{CC} = 5 \text{ V}$	t_{off}		25		μs

SAFETY AND INSULATION RATINGS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Climatic classification (according to IEC 68 part 1)				55/100/21		
Comparative tracking index		CTI	175		399	
V_{IOTM}			10000			V
V_{IORM}			890			V
P_{SO}					400	mW
I_{SI}					275	mA
T_{SI}					175	°C
Creepage distance	standard DIP-4		7			mm
Clearance distance	standard DIP-4		7			mm
Creepage distance	400 mil DIP-4		8			mm
Clearance distance	400 mil DIP-4		8			mm
Insulation thickness, reinforced rated	per IEC 60950 2.10.5.1		0.4			mm

Note

As per IEC 60747-5-2, § 7.4.3.8.1, this optocoupler is suitable for "safe electrical insulation" only within the safety ratings. Compliance with the safety ratings shall be ensured by means of protective circuits.

TYPICAL CHARACTERISTICS

T_{amb} = 25 °C, unless otherwise specified

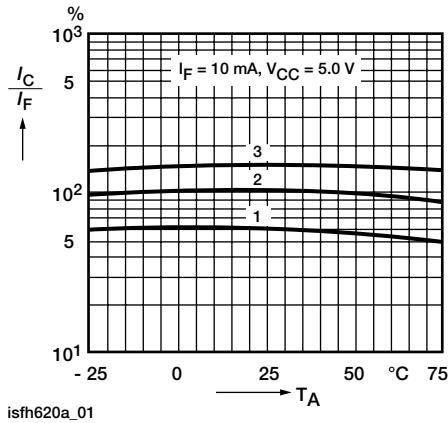


Fig. 2 - Current Transfer Ratio (CTR) vs. Temperature

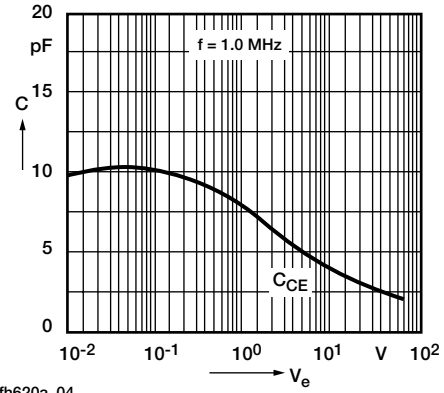


Fig. 5 - Transistor Capacitance (Typ.) vs. Collector Emitter Voltage

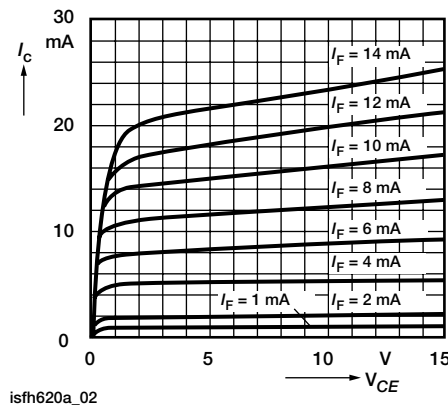


Fig. 3 - Output Characteristics (Typ.) Collector Current vs. Collector Emitter Voltage

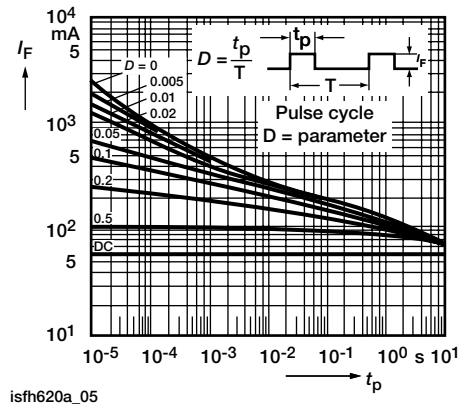


Fig. 6 - Permissible Pulse Handling Capability Forward Current vs. Pulse Width

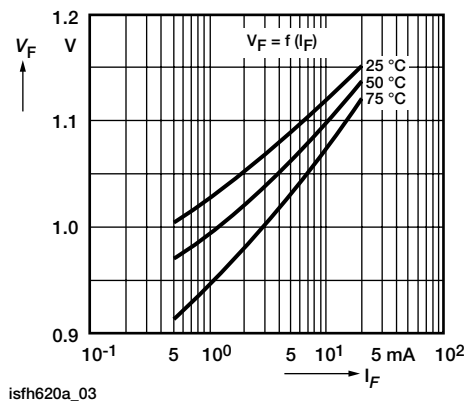


Fig. 4 - Diode Forward Voltage (Typ.) vs. Forward Current

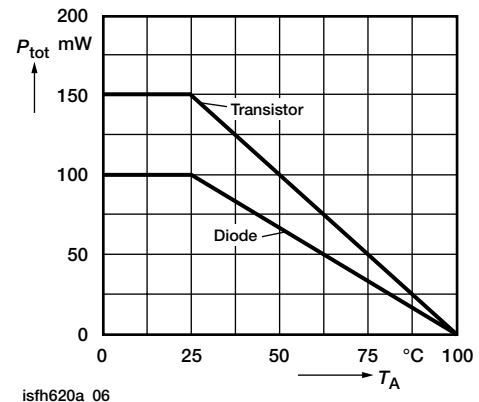


Fig. 7 - Permissible Power Dissipation vs. Ambient Temperature

SFH620AA, SFH620AGB



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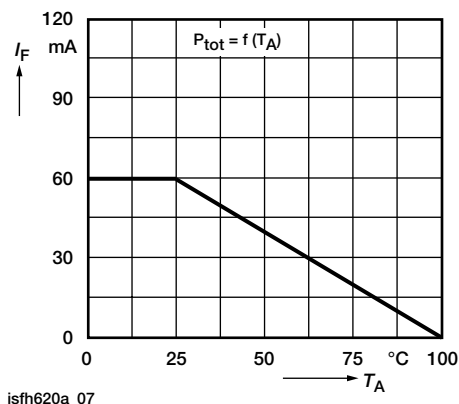
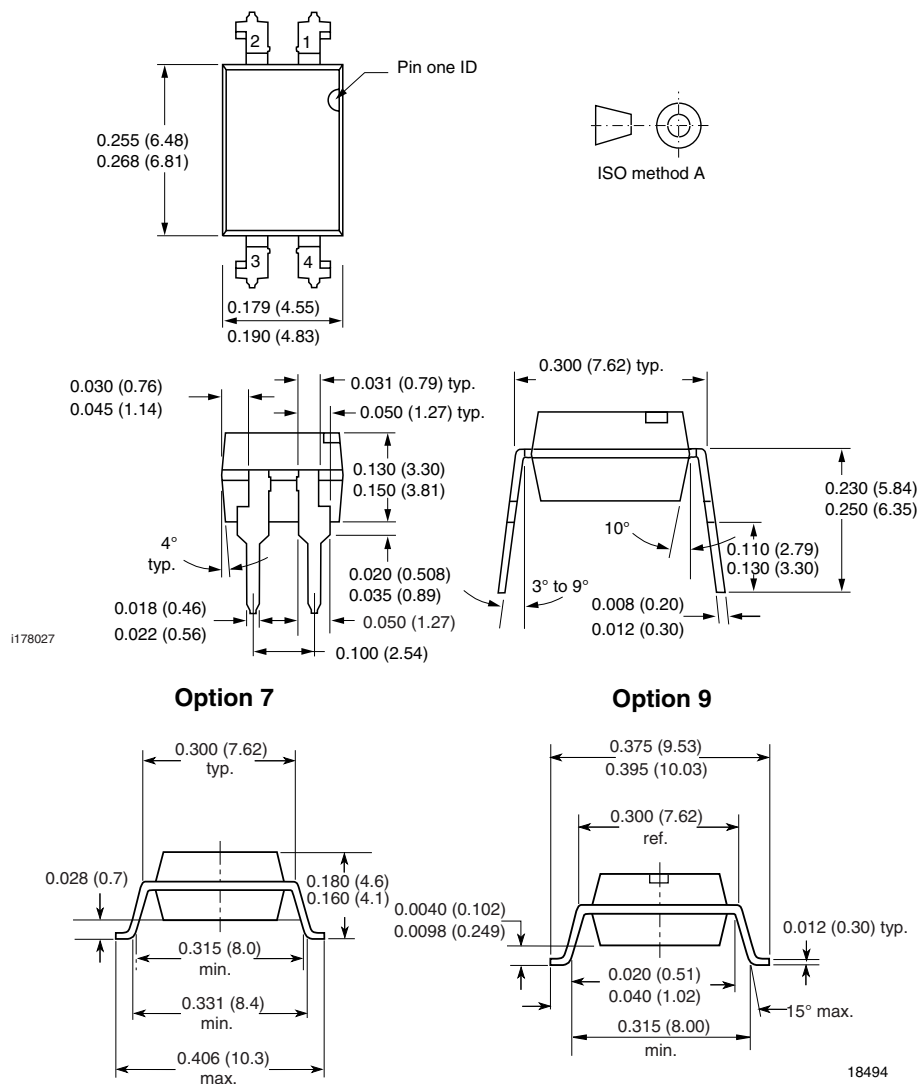


Fig. 8 - Permissible Diode Forward Current vs. Ambient Temperature

PACKAGE DIMENSIONS in inches (millimeters)



**OZONE DEPLETING SUBSTANCES POLICY STATEMENT**

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively.
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA.
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design
and may do so without further notice.

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Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany

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